



# **PRODUCT DATA SHEET**



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Datasheet

Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO\_questions@jgsemi.com.



**ESD Protection Diode Array** 

#### **Features**

- 40Watts peak pulse power (tp = 8/20µs)
- Tiny SOT143 package
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance (Cj=0.35pF typ I/O to I/O.)
- Protection one data/power line
- IEC 61000-4-2 ±15kV contact ±20kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 3.5A(8/20µs)



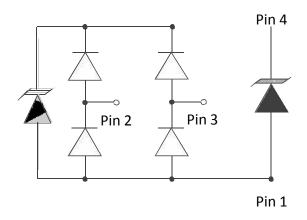
### **Applications**

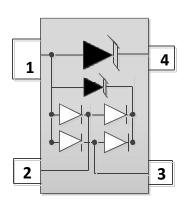
- USB2.0,
- Ethernet
- Notebooks, Desktops, and Servers
- Video Line Protection

### **Mechanical Data**

- SOT143 package
- Molding compound flammability rating: UL94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

## **Schematic & PIN Configuration**







**Absolute Maximum Rating** 

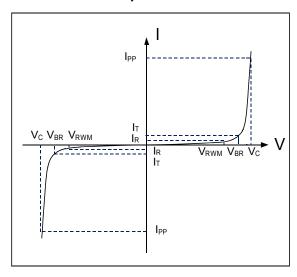
Rating	Symbol	Value	Units
Peak Pulse Power ( t <sub>p</sub> =8/20μs)	P <sub>PP</sub>	40	Watts
Peak Pulse Current ( t <sub>p</sub> =8/20μs ) (note1)	I <sub>pp</sub>	3.5	А
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V <sub>ESD</sub>	20 15	kV
Lead Soldering Temperature	TL	260(10seconds)	℃
Junction Temperature	TJ	-55 to + 125	℃
Storage Temperature	T <sub>stg</sub>	-55 to + 125	℃

### **Electrical Characteristics**

Parameter	Symbol	Conditions Min		Typical	Max	Units
Reverse Stand-Off Voltage	$V_{RWM}$				5.0	V
Reverse Breakdown Voltage	$V_{BR}$	I <sub>T</sub> =1mA	6.0	7.2		V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> =5V,T=25℃		50	500	nA
Clamping Voltage	V <sub>C</sub>	I <sub>PP</sub> =3.5A,t <sub>p</sub> =8/20μs		10		V
Junction Capacitance	C <sub>j</sub>	V <sub>R</sub> = 0V, f = 1MHz IO to IO		0.35		
		V <sub>R</sub> = 0V, f = 1MHz IO to GND		0.65		pF

# **Electrical Parameters (TA = 25°C unless otherwise noted)**

Symbol	Parameter
IPР	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @ IPP
V <sub>RWM</sub>	Working Peak Reverse Voltage
lR	Maximum Reverse Leakage Current @ V <sub>RWM</sub>
V <sub>BR</sub>	Breakdown Voltage @ I⊤
lτ	Test Current



Note: 8/20µs pulse waveform.



## **Typical Characteristics**

Figure 1: Peak Pulse Power vs. Pulse Time

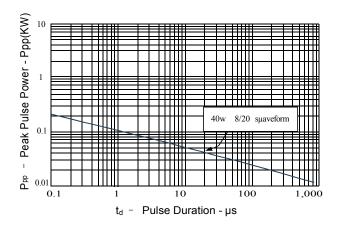


Figure 2: Power Derating Curve

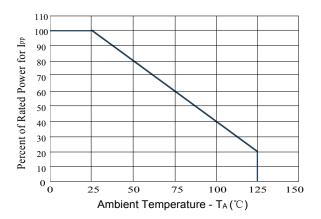


Figure3: Pulse Waveform

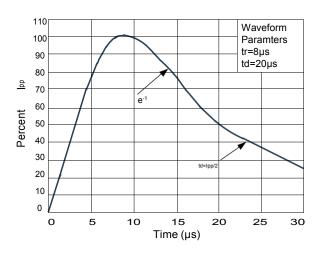
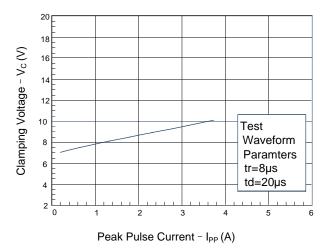
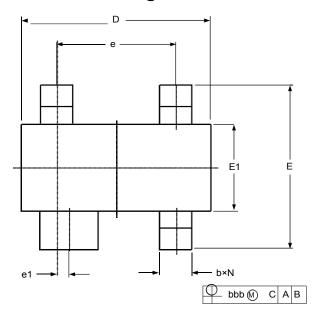


Figure 4: Clamping Voltage vs.lpp

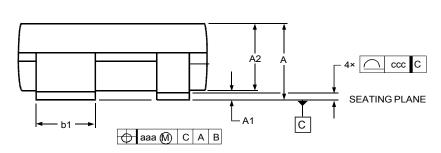


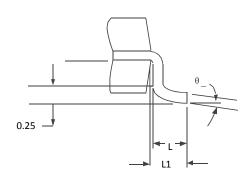


# **Outline Drawing - SOT143**



DIMENSIONS					
SYMBOL	MILLIMETER		INCHES		
	MIN	MAX	MIN	MAX	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
b1	0.750	0.900	0.030	0.035	
D	2.800	3.000	0.110	0.118	
е	1.800	2.000	0.071	0.079	
e1	0.200TYP		0.008TYP		
E	2.250	2.550	0.089	0.100	
E1	1.200	1.400	0.047	0.055	
θ	0°	8°	0°	8°	
aaa	.006		0.15		
bbb	.008		0.20		
ccc	.004		0.10		







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